



IPB083N10N3 G Information



For Reference Only

Part Number IPB083N10N3 G
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 80A TO263-3

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPB083N10N3 G Specifications

Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.5V @ 75μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3980pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.5V @ 75μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs8.3 mOhm @ 73A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.5V @ 75μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs8.3 mOhm @ 73A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO263-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	OptiMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 75μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case 100V 80A (Tc) 80B (Tc) 8	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.5V @ 75µA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3980pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 75μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 3.5V @ 75μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3980pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Noperating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 55nC @ 10V 3980pF @ 50V +20V FET Feature - Surface Mount 125W (Tc) Surface Mount Surface Mount TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	3.5V @ 75μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	55nC @ 10V
FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	3980pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 8.3 mOhm @ 73A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	125W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	8.3 mOhm @ 73A, 10V
Supplier Device Package PG-TO263-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	PG-TO263-2
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

IPB083N10N3 G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPB083N10N3 G Payment Methods



















IPB083N10N3 G Shipping Methods













If you have any question about IPB083N10N3 G, please do not hesitate to contact us!

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